

AMENDMENTS TO THE CLAIMS

Claim 1 (amended) A multideposition sub-atmospheric chemical vapor deposition (SACVD) reactor comprising:

a substrate processing chamber;

A  
a carbon susceptor adapted to hold a substrate in said substrate processing chamber during a SACVD operation, wherein said carbon susceptor ~~consists~~ is coated by a polysilicon film to protect it against said cleaning gases, wherein said polysilicon coating comprises a bottom polysilicon coating and a top polysilicon coating;

a gas distribution system ~~adapted to introduce gases into said substrate processing chamber and~~ including appropriate valves, gas supply lines and other equipment adapted necessary to flow gases into said substrate processing chamber, wherein said gases include dielectric and / non-dielectric forming gases and in-situ cleaning gases that are aggressive to carbon;

a heating system to heat said susceptor to an adequate deposition temperature;

a pressurization system adapted to set a pressure level within said substrate processing chamber; and

a controller coupled to said gas distribution system and pressurization system for directing operation of said SACVD reactor.

Claim 2 (original) The SACVD reactor of claim 1 wherein said dielectric material is  $\text{Si}_3\text{N}_4$  and said forming gas is a  $\text{SiH}_4/\text{NH}_3$  mixture.

Claim 3 (original) The SACVD reactor of claim 1 wherein said dielectric material is  $\text{SiO}_2$  and said forming gas is a  $\text{SiH}_4/\text{NO}_2$  mixture.

Claim 4 (original) The SACVD reactor of claim 1 wherein said dielectric material is  $\text{SiON}$  and said forming gas is either a  $\text{DCS}/\text{N}_2\text{O}/\text{NH}_3$  mixture or a  $\text{SiH}_4/\text{N}_2\text{O}/\text{NH}_3$  mixture.

Claim 5 (original) The SACVD reactor of claim 1 wherein said non-dielectric material is doped polysilicon and said forming gas is a  $\text{SiH}_4/\text{PH}_3$  mixture.

Claim 6 (original) The SACVD reactor of claim 2 wherein said cleaning gases are selected from the group consisting of  $\text{NF}_3$  and  $\text{HCl}$ .

Claim 7 (original) The SACVD reactor of claim 1 wherein said dielectric material is  $\text{Si}_3\text{N}_4$  and said deposition is performed in a Centura HTF reactor at a pressure of about 80 Torr to about 150 Torr, at a temperature of about 650 °C to about 800 °C, with a  $\text{NH}_3$  flow of about 3.2 slm, with a  $\text{SiH}_4$  flow of about 30 sccm, with a  $\text{N}_2$  flow of about 5 slm, and for a duration of about 5 min.

AI  
Cont  
Claim 8 (original) The SACVD reactor of claim 1 wherein said dielectric material is  $\text{SiO}_2$  and said deposition is performed in a Centura HTF reactor at a pressure of about 50 Torr to about 100 Torr, at a temperature of about 600 °C to about 900 °C, with a  $\text{SiH}_4$  flow of about 60 sccm, with a  $\text{N}_2\text{O}$  flow of about 2.8 slm, and with a  $\text{N}_2$  flow of about 9.2 slm.

Claim 9 (original) The SACVD reactor of claim 1 wherein said dielectric material is  $\text{SiON}$  and said deposition is performed in a Centura HTF reactor at a pressure of about 80 Torr to about 150 Torr, at a temperature of about 650 °C to about 800 °C, with a  $\text{NH}_3$  flow of about 1 slm, with a DCS flow of about 200 sccm, with a  $\text{N}_2\text{O}$  flow of about 2.8 slm, and with a  $\text{N}_2$  flow of about 5 slm.

Claims 10-14 (canceled)

Claim 15 (amended) A susceptor for dielectric and non-dielectric material deposition in a SACVD reactor resistant to  $\text{NF}_3$  attack comprising a carbon plate coated by a polysilicon film, wherein said polysilicon coating comprises a bottom polysilicon coating and a top polysilicon coating.

Claim 16 (currently amended) A susceptor for dielectric and non-dielectric material deposition in a SACVD reactor resistant to  $\text{NF}_3$  attack comprising a carbon plate coated by a polysilicon film. ~~The susceptor of claim 15 wherein said polysilicon coating comprises a bottom polysilicon coating and a top polysilicon coating of different thicknesses, and said bottom polysilicon coating has a thickness of about 4  $\mu\text{m}$  and said top polysilicon coating has a thickness of about 1.5  $\mu\text{m}$ .~~

Claim 17 (new) The susceptor of Claim 15, wherein said polysilicon coating comprises a bottom polysilicon coating and a top polysilicon coating of different thicknesses.

Claim 18 (new) The SACVD reactor of Claim 1, wherein said polysilicon coating comprises a bottom polysilicon coating and a top polysilicon coating of different thicknesses.

AI  
cont  
Claim 19 (new) The SACVD reactor of Claim 18, wherein said bottom polysilicon coating has a thickness of about 4  $\mu\text{m}$  and said top polysilicon coating has a thickness of about 1.5  $\mu\text{m}$ .

Claim 20 (new) The SACVD reactor of Claim 1, wherein said substrate processing chamber has upper and lower volumes separated by said carbon susceptor, and said gas distribution system includes first and second gas injection means for respectively injecting gases in the upper and lower volumes of the processing chamber.

---